General Description

SFGMOS® AE87F e TSeWW a AdWfS EW a Vg fade g cgWWWh WWWeY fa S ZWWWlow $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low V_{th} series is specially designed to use in synchronous rectification power systems with low driving voltage.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

RoHS compliant

Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

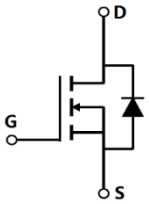
Key Performance Parameters

Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	100	V
$I_{D,\ pulse}$	120	A
$R_{DS(ON)\ max}$ @ V_{GS}=10V	20	
Q_g	19.8	nC

Marking Information

Product Name	Package	Marking
SFG10R20PF	TO220	SFG10R20P

Package & Pin information



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Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	±20	V
Continuous drain current[1)], T_C=25 °C	I_D	40	A
Pulsed drain current[2)], T_C=25 °C	$I_{D, pulse}$	120	A
Continuous diode forward current[1)], T_C=25 °C	I_S	40	A
Diode pulsed current[2)], T_C=25 °C	$I_{S, Pulse}$	120	A
Power dissipation[3)], T_C=25 °C	P_D	72	W
Single pulsed avalanche energy[5)]	E_{AS}	30	mJ
Operation and storage temperature	T_{stg} T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R 5	1.74	°C/W
Thermal resistance, junction-ambient[4)]	R 3	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	V_{GS}=0 V, I_D=250 A
Gate threshold voltage	$V_{GS(th)}$	1.0		2.5	V	V_{DS}=V_{GS}, I_D=250 A
Drain-source on-state resistance	$R_{DS(ON)}$		17	20		V_{GS}=10 V, I_D=8 A
Drain-source on-state resistance	$R_{DS(ON)}$			26		V_{GS}=4.5 V, I_D=6 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	A	V_{DS}=100 V, V_{GS}=0 V

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Dynamic Characteristics

Parameter	Symbol	Min.

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Electrical Characteristics Diagrams

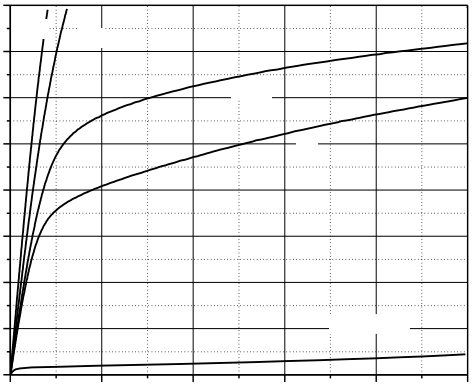

Figure 1. Typ. output characteristics

Figure 2. Typ. transfer characteristics

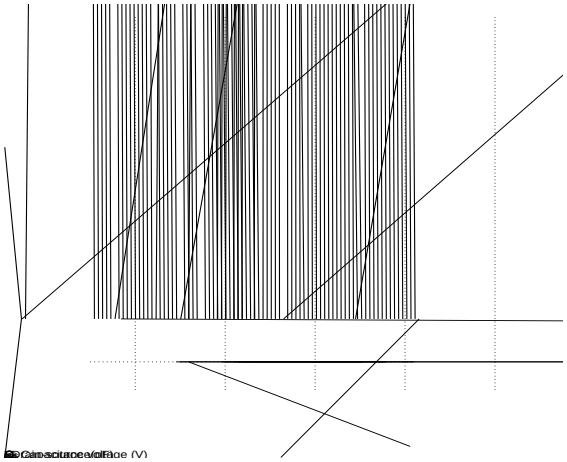

Figure 3. Typ. capacitances

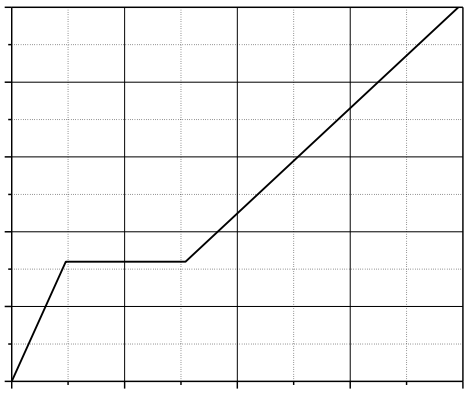

Figure 4. Typ. gate charge

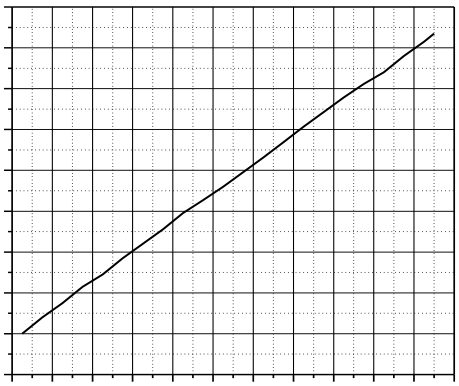

Figure 5. Drain-source breakdown voltage

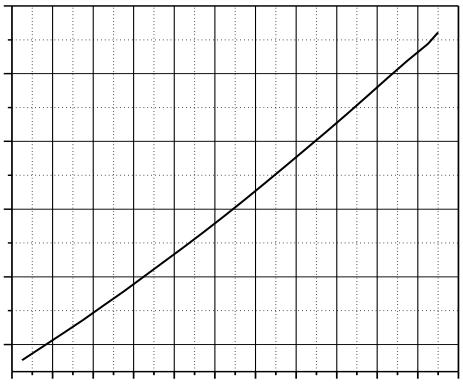

Figure 6. Drain-source on-state resistance

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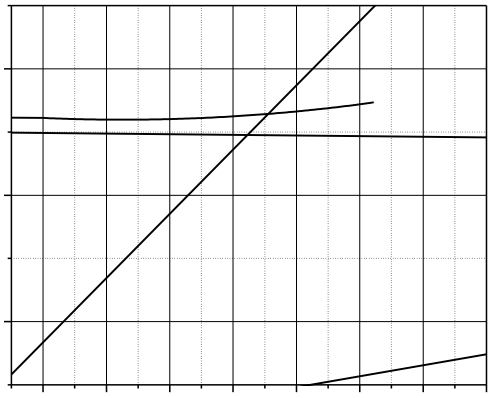

Figure 7. Drain-source on-state resistance

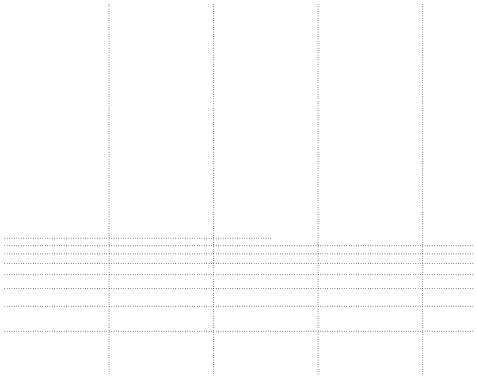

Figure 8. Forward characteristic of body diode

Figure 9. Safe operation area T_C=25 °C

Test circuits and waveforms

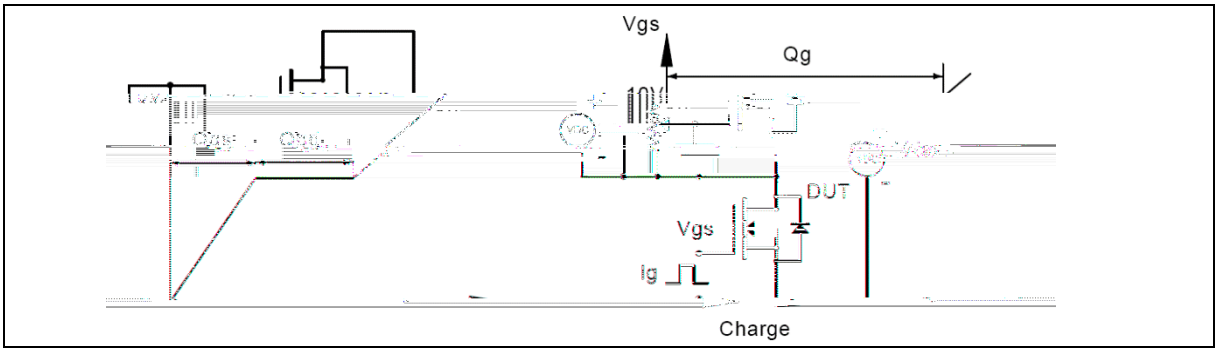

Figure 1. Gate charge test circuit & waveform

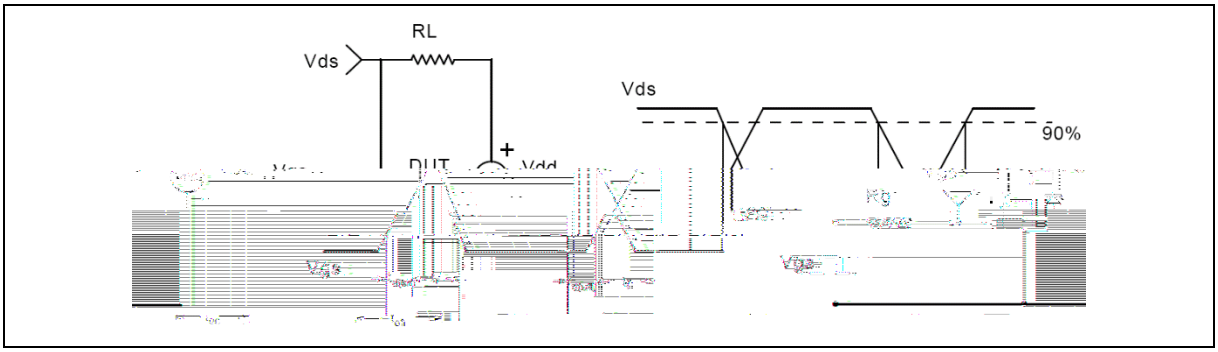

Figure 2. Switching time test circuit & waveforms

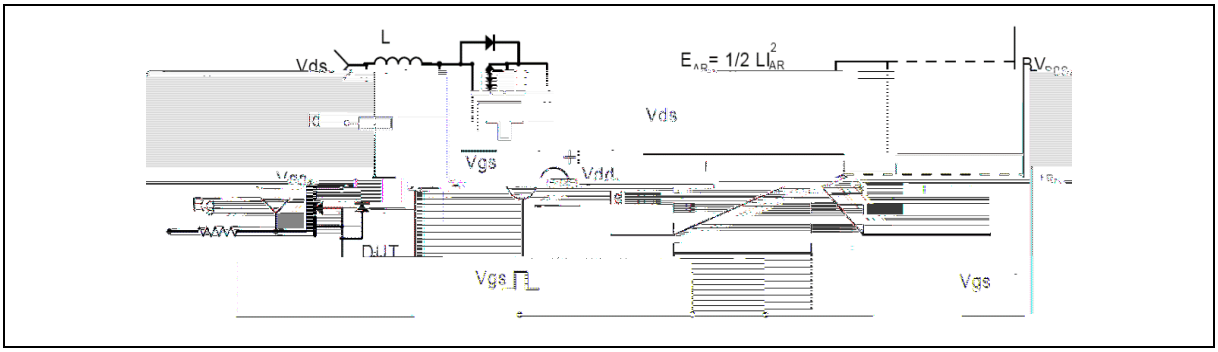

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

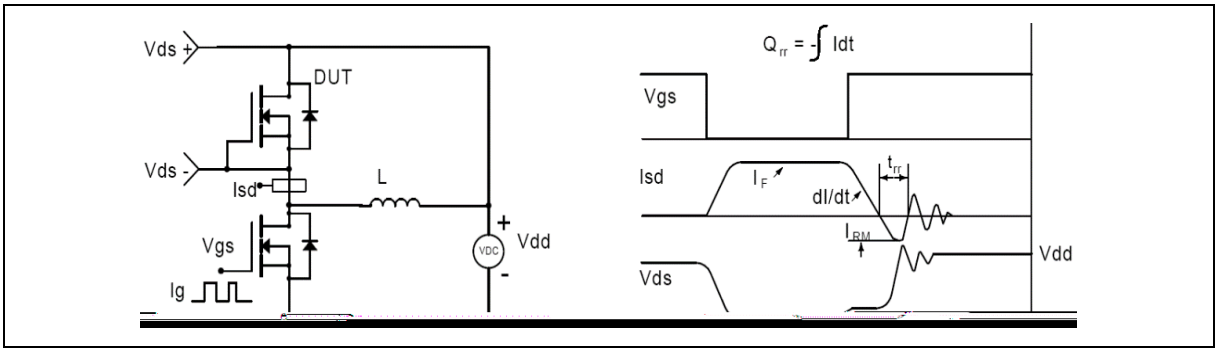

Figure 4. Diode reverse recovery test circuit & waveforms

Package Information

Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-		

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Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-J	50	20	1000	5	5000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG10R20PF	TO220	yes	yes	yes

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